Customer No. 22,852
Attorney Docket No. 04329.3139

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:	)	
	)	
Mitsuaki IZUHA et al.	)	
	)	Group Art Unit:
Serial No.: Not Yet Assigned	)	
	)	Examiner:
Filed: September 12, 2003	)	
	)	
For: MOSFET FORMED BY USING SALICIDE PROCESS AND METHOD OF MANUFACTURING THE SAME	)	

MAIL STOP PATENT APPLICATION
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

Pursuant to 37 C.F.R. §§1.56 and 1.97(b), applicants bring to the Examiner's attention the documents listed on attached Form PTO-1449. Copies of the non-U.S. patent documents are attached. Applicants respectfully request that the Examiner consider the documents listed on attached Form PTO-1449 and indicate that they were considered by making an appropriate notation on this form.

This Information Disclosure Statement is being filed with the above-referenced application.

The following is a concise statement of relevance of the non-English language documents:

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1. Japanese Patent Laid Open (KOKAI) No. 09-139511 discloses a method to decrease contact resistance in a semiconductor apparatus by ion implantation of Ge to Si substrate.

2. Japanese Patent Publication (TOROKU) 3219996 discloses a method to decrease contact resistance in a semiconductor apparatus by ion implantation of Ge to Si substrate.

This submission does not represent that a search has been made or that no better art exists and does not constitute an admission that each or all of the listed documents are material or constitute "prior art." If the Examiner applies any of the documents as prior art against any claim in the application and applicants determine that the cited documents do not constitute "prior art" under United States law, applicants reserve the right to present to the office the relevant facts and law regarding the appropriate status of such documents. Applicants further reserve the right to take appropriate action to establish the patentability of the disclosed invention over the listed documents, should one or more of the documents be applied against the claims of the present application.

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If there is any fee due in connection with the filing of this Statement, please charge the fee to our Deposit Account No. 06-0916.

Respectfully submitted,

FINNEGAN, HENDERSON, FARABOW, GARRETT & DUNNER, L.L.P.

Dated: September 12, 2003

By: _____
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Enclosures
RVB/FPD/gah

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OMB No. 0651-0011

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.3139	Serial No.	
Applicant	Mitsuaki IZUHA et al.		
Filing Date	September 12, 2003	Group:	

U.S. PATENT DOCUMENTS

Examiner Initial*		Document Number	Issue Date (Pub. Date)	Name	Class	Sub Class	Filing Date If Appropriate
		5,656,859	08/12/1997	Murakoshi et al.			
		5,770,512	06/23/1998	Murakoshi et al.			
		2002/0130393 A1	(09/19/2002)	Takayanagi et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No
		9-139511	05/27/1997	Japan			No
		3219996	08/10/2001	Japan			No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Ku et al.; "HIGH PERFORMANCE pMOSFETs WITH Ni(Si_XGe_{1-X})/POLY-$Si_{0.8}Ge_{0.2}$ GATE"; Symposium on VSLI Technology Digest of Technical Papers, (2000)

Examiner	Date Considered
*Examiner:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
Form PTO 1449	Patent and Trademark Office - U.S. Department of Commerce